Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- · Logic-level compatible
- · Very fast switching
- · Enhanced power dissipation capability of 1.4 W
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

3. Applications

- · Relay driver
- · High-speed line driver
- · High-side loadswitch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	-30	V
V_{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	$V_{GS} = -10 \text{ V}; T_{amb} = 25 ^{\circ}\text{C}; t \le 5 \text{ s}$	[1]	-	-	-4.4	Α
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = -10 V; I_D = -3.3 A; T_j = 25 °C		-	60	80	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

Symbol	Description	Simplified outline	Graphic symbol	
D	drain	<u> </u>	D	
D	drain			
G	gate	O H1 H2 H3		G \downarrow \downarrow \downarrow
S	source	TSOP6 (SOT457)		
D	drain			
D	drain		S 017aaa259	
	D D G S D	D drain D drain G gate S source D drain	D drain D drain G gate S source TSOP6 (SOT457) D drain	

6. Ordering information

Table 3. Ordering information

Type number		Package					
		Name	Description	Version			
	PMN70EPE	TSOP6	plastic surface-mounted package (TSOP6); 6 leads	SOT457			

7. Marking

Table 4. Marking codes

Type number	Marking code
PMN70EPE	G2

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-30	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = -10 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-4.4	Α
		V _{GS} = -10 V; T _{amb} = 25 °C	[1]	-	-3.3	Α
		V _{GS} = -10 V; T _{amb} = 100 °C	[1]	-	-2.1	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-14	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	570	mW
			[1]	-	1.4	W
		T _{sp} = 25 °C		-	6.25	W
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain d	iode				<u>'</u>	
I _S	source current	T _{amb} = 25 °C	[1]	-	-1.4	Α

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

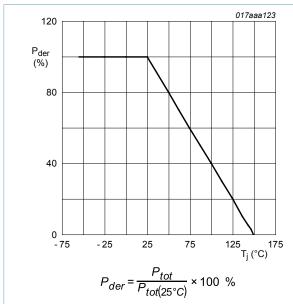


Fig. 1. Normalized total power dissipation as a function of junction temperature

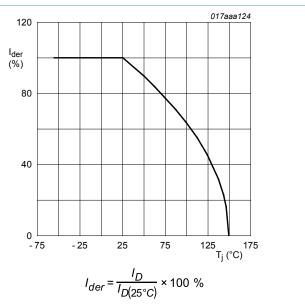
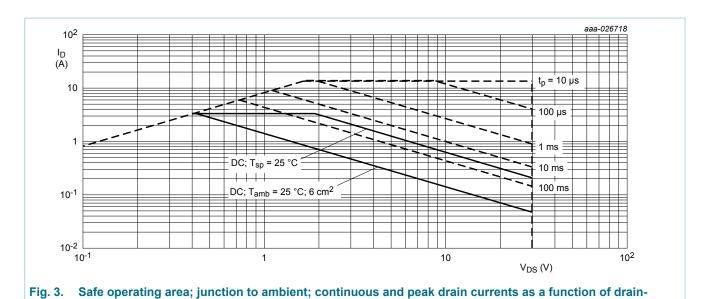


Fig. 2. Normalized continuous drain current as a function of junction temperature

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source voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
froi	thermal resistance		[1]	-	190	220	K/W
	from junction to ambient		[2]	-	78	90	K/W
		in free air; t ≤ 5 s	[2]	-	47	54	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	15	20	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

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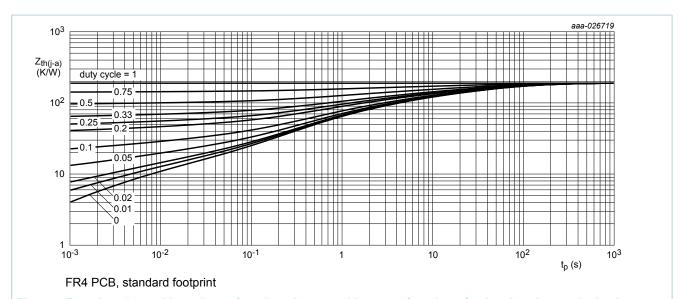


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

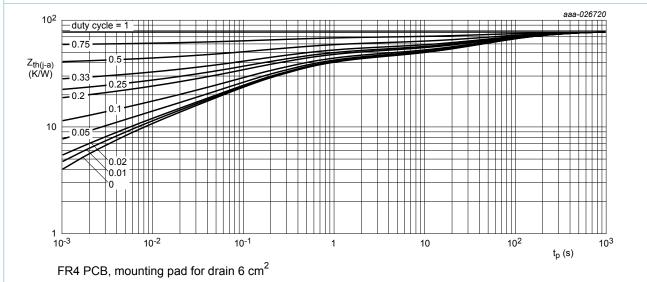


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

30 V, P-channel Trench MOSFET

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					,
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	-30	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	-1	-2	-3	V
I _{DSS}	drain leakage current	V _{DS} = -30 V; V _{GS} = 0 V; T _j = 25 °C	-	-	-1	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μΑ
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μΑ
		V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	1	μΑ
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-1	μΑ
		V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		$V_{GS} = -4.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	-100	nA
R _{DSon}	drain-source on-state	V_{GS} = -10 V; I_D = -3.3 A; T_j = 25 °C	-	60	80	mΩ
	resistance	V_{GS} = -10 V; I_D = -3.3 A; T_j = 150 °C	-	91	121	mΩ
		V_{GS} = -4.5 V; I_D = -2.6 A; T_j = 25 °C	-	96	140	mΩ
9 _{fs}	forward transconductance	V_{DS} = -10 V; I_D = -2 A; T_j = 25 °C	-	12.6	-	S
R_G	gate resistance	f = 1 MHz; T _j = 25 °C	-	12	-	Ω
Dynamic ch	naracteristics					-
Q _{G(tot)}	total gate charge	V_{DS} = -15 V; I_D = -3.3 A; V_{GS} = -10 V;	-	6.5	11.5	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	1.2	-	nC
Q_{GD}	gate-drain charge		-	1.2	-	nC
C _{iss}	input capacitance	$V_{DS} = -15 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$	-	370	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	64	-	pF
C _{rss}	reverse transfer capacitance		-	44	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -15 V; I_D = -3.3 A; V_{GS} = -10 V;	-	5	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$	-	8	-	ns
t _{d(off)}	turn-off delay time		-	19	-	ns
t _f	fall time		-	7.5	-	ns
Source-dra	in diode		'	,	•	
	source-drain voltage	I _S = -1.4 A; V _{GS} = 0 V; T _j = 25 °C			-1.2	V

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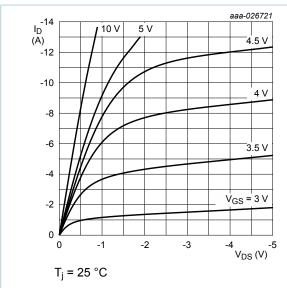


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

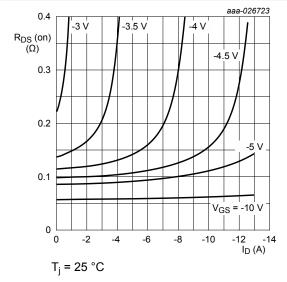


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

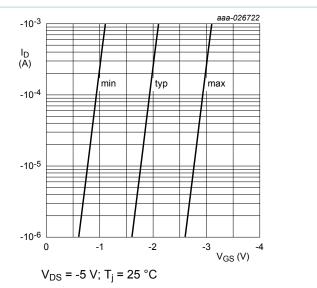


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

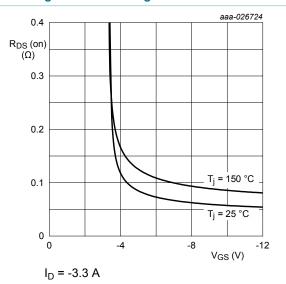


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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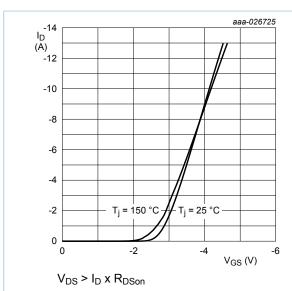


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

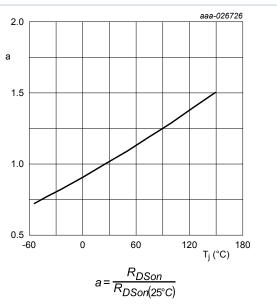


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

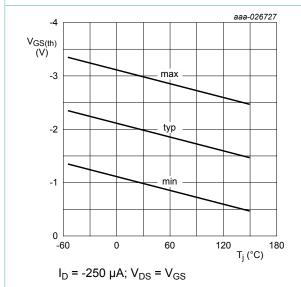


Fig. 12. Gate-source threshold voltage as a function of junction temperature

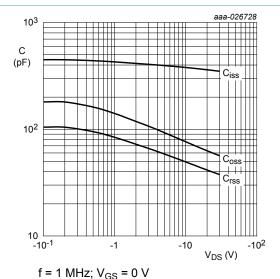


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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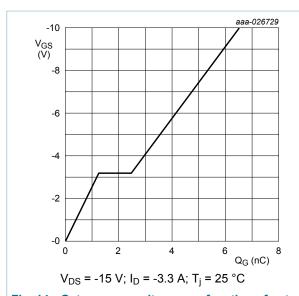


Fig. 14. Gate-source voltage as a function of gate charge; typical values

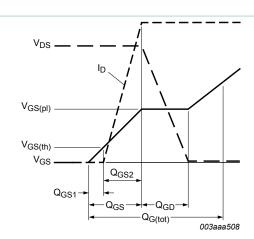


Fig. 15. Gate charge waveform definitions

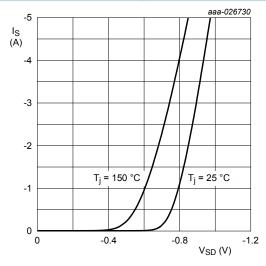
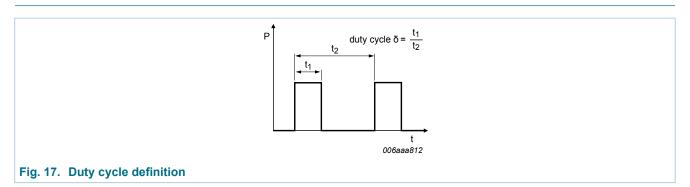


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

 $V_{GS} = 0 V$



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12. Package outline

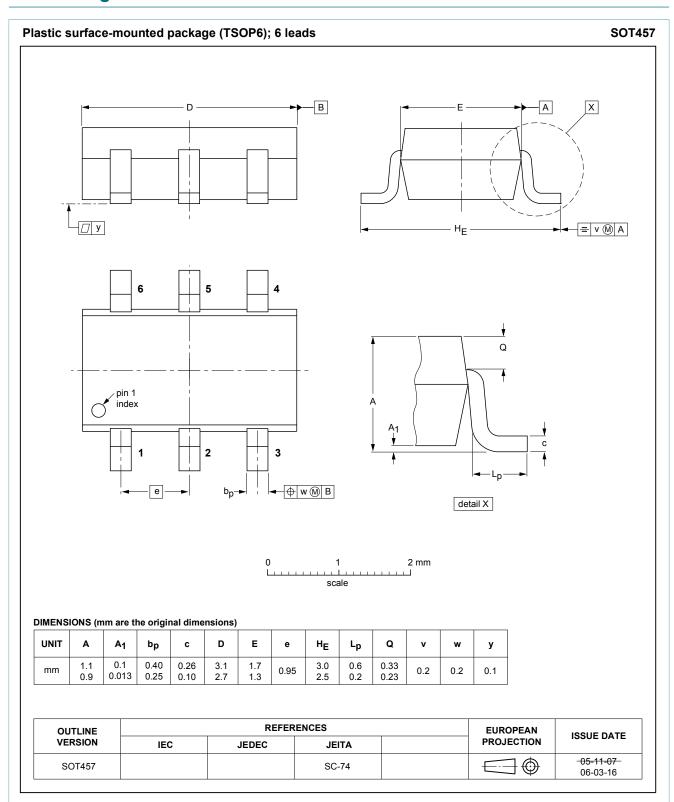
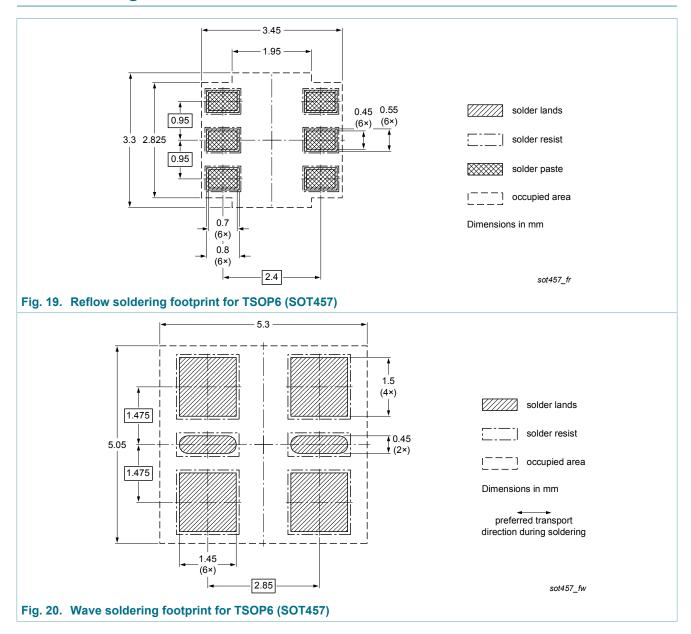


Fig. 18. Package outline TSOP6 (SOT457)

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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMN70EPE v.1	20170523	Product data sheet	-	-

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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